

## **SFT353 Transistor Datasheet. Parameters and Characteristics.**

Type Designator: SFT353

Material of transistor: Ge

Polarity: pnp

Maximum collector power dissipation ( $P_c$ ): 200mW

Maximum collector-base voltage ( $U_{cb}$ ): 24V

Maximum collector-emitter voltage ( $U_{ce}$ ):

Maximum emitter-base voltage ( $U_{eb}$ ): 12V

Maximum collector current ( $I_c$  max): 150mA

Maximum junction temperature ( $T_j$ ): 85°C

Transition frequency ( $f_t$ ): 1MHz

Collector capacitance ( $C_c$ ), Pf: 50

Forward current transfer ratio ( $h_{FE}$ ), min/max: 80T

Manufacturer of SFT353 transistor: MISTRAL

Package of SFT353 transistor: TO1